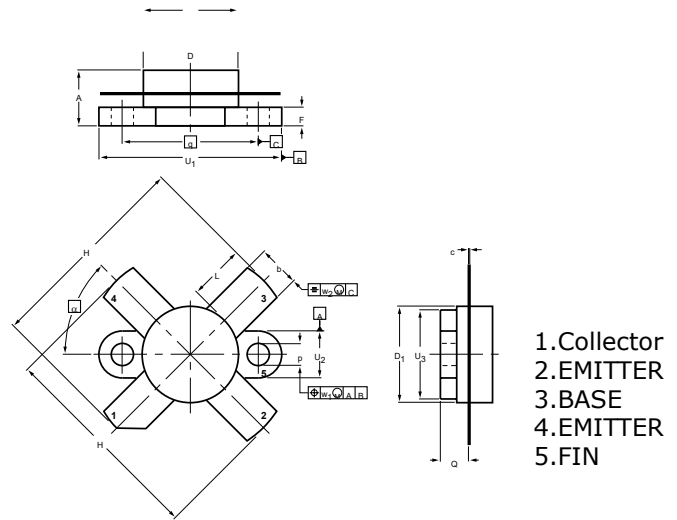


DESCRIPTION

Designed primarily for applications as high-power linear power amplifier from 2.0 to 30MHz

FEATURES

- Specified 28V, 30MHz Characteristics
- $P_o = 150W$ PEP
- $G_p = 13$ Typ. min. at 150 W/30MHz
- IMD3 = -30 dBc max. at 150 W(PEP)
- Omnidgold™ Metalization System



1. Collector
2. EMITTER
3. BASE
4. EMITTER
5. FIN

DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27	5.82	0.16	12.86	12.83	2.67	28.45	7.93	3.30	4.45	18.42	24.90	6.48	12.32	0.51	1.02	45°
	6.17	5.56	0.10	12.59	12.57	2.41	25.52	6.32	3.05	3.91		24.63	6.22	12.06			
inches	0.286	0.229	0.006	0.506	0.505	0.105	1.120	0.312	0.130	0.175	0.725	0.98	0.255	0.485	0.02	0.04	
	0.243	0.219	0.004	0.496	0.495	0.095	1.005	0.249	0.120	0.154		0.97	0.245	0.475			

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CB0}	65	V
Collector-Emitter Voltage	V_{CES}	65	V
Collector-Emitter Voltage	V_{CEO}	35	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	20	A
Collector Power Dissipation	P_{DISS}	290	W
Junction Temperature	T_J	-65 to 150	°C
Storage Temperature Range	T_{STG}	-65 to 150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=200mA, I_B=0$	35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=100mA, V_{EB}=0$	65	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	3	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=5A$	15	30	120	
Collector Output Capacitance	C_{ob}	$V_{CB}=12.5V, I_E=0$ $f=1MHz$	-	420	-	pF
Power Gain	G_p	$V_{CC}=28V, P_{OUT}=150W$ $I_{CQ}=150mA, f=30MHz$	10	13	-	dB
Collector Efficiency	η_C		-	45	-	%
Intermodulation Distortion	IMD3		-	-33	-30	dBc
Series Equivalent Input Impedance	Z_{IN}	$V_{CC}=28V, P_{OUT}=150W$ $f=30MHz$	-	0.81 - j0.26	-	Ω

Note : Above parameters , ratings , limits and conditions are subject to change .